

L Number	Hits	Search Text	DB	Time stamp
1	203	semiconductor and ((tungste or W) same deposit\$4 same (CVD with PVD))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:41
2	14	(semiconductor and ((tungste or W) same deposit\$4 same (CVD with PVD))) and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:31
3	1781	(438/106-110).CCLS.	USPAT	2002/11/27 22:40
4	1	((438/106-110).CCLS.) and (tungste or W) and LTO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:41
5	1	((438/106-110).CCLS.) and (tungste or W) and (low with temperature with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:45
6	38	semiconductor and SOI and (substrate with bond\$4) and (tungste or W) and (low with temperature with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:44
8	5	((438/106-110).CCLS.) and (tungsten) and (low with temperature with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:45
7	25	semiconductor and SOI and (substrate with bond\$4) and (tungsten) and (low with temperature with oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:48
9	0	semiconductor and SOI and (substrate with bond\$4) and (tungsten) and (low with temperature with oxide) and (oxygen with migration)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:49
10	5	semiconductor and (substrate with bond\$4) and ((tungsten) same barrier same (low with temperature with oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/27 22:49

-	12	((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)) and silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:30
-	0	semiconductor and ((tungsten or W) same silicide same UHV same deporption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 15:32
-	46	semiconductor and ((tungsten or W) same silicide same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 15:32
-	1	semiconductor and ((tungsten or W) same silicide same UHV same desorption same (silane or "SiH.sub.4") same (ammonia or "NH.sub.3"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 15:41
-	1	semiconductor and ((tungsten with silicide) or (WSi or WSiN)).ti. and silane and ammonia	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 15:42
-	2	semiconductor and ((WSiN) same silane same ammonia)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 15:45
-	2518	semiconductor and (nitrid\$6 same tungsten adj silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 15:48

-	411	(semiconductor and (nitrid\$6 same tungsten adj silicide)) and silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:56
-	146	((semiconductor and (nitrid\$6 same tungsten adj silicide)) and silane) and ammonia	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:52
-	6	semiconductor and (monolayer with (tungsten adj silicide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:56
-	0	(semiconductor and (monolayer with (tungsten adj silicide))) and silane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:56
-	1	((semiconductor and (nitrid\$6 same tungsten adj silicide)) and silane) and nitrad\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:31
-	92	semiconductor and (electroplating same electrolessly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:32
-	54	semiconductor and (electroplating with electrolessly)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:35
-	0	semiconductor and (electroplating with electrolessly with equivalent)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 16:35

-	70	(US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.	USPAT; US-PGPUB	2002/11/26 14:41
-	17	((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and adhesive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:06

L Number	Hits	Search Text	DB	Time stamp
-	0	(semiconductor and (back with gate) and (tungsten or W) and adhesive and SOI) and LTO	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 13:35
-	42	semiconductor and (back with gate) and (tungsten or W) and adhesive and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 13:42
-	453	semiconductor and SOI and (tungsten or W) and multilayer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 13:52
-	41	(semiconductor and SOI and (tungsten or W) and multilayer) and adhesive	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 13:54
-	36	((semiconductor and SOI and (tungsten or W) and multilayer) and adhesive) not (semiconductor and (back with gate) and (tungsten or W) and adhesive and SOI)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 13:58
-	2992	((438/622) or (438/582-583) or (438/195) or (438/266) or (438/311) or (438/455) or (438/591) or (438/682-683)).CCLS.	USPAT; US-PGPUB	2002/11/26 14:09
-	213	((438/622) or (438/582-583) or (438/195) or (438/266) or (438/311) or (438/455) or (438/591) or (438/682-683)).CCLS.) and (back with gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 14:18
-	1345	((438/455) or (438/406) or (438/459) or (438/479)).CCLS.	USPAT; US-PGPUB	2002/11/26 14:28
-	525	((438/455) or (438/406) or (438/459) or (438/479)).CCLS.) and (tungsten or W)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/11/26 14:29

-	56	((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:23
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-	51	((US-6362078-\$ or US-6057212-\$ or US-4335391-\$ or US-6455398-\$ or US-6429095-\$ or US-6429094-\$ or US-6417075-\$ or US-6410436-\$ or US-6333202-\$ or US-6313012-\$ or US-6306729-\$ or US-6221738-\$ or US-6150031-\$ or US-6146979-\$ or US-6143628-\$ or US-6121112-\$ or US-6103598-\$ or US-6103009-\$ or US-6100165-\$ or US-6054363-\$ or US-6045626-\$ or US-5985739-\$ or US-5966620-\$ or US-5937312-\$ or US-5856229-\$ or US-5773355-\$).did. or (US-5670411-\$ or US-5536361-\$ or US-5492859-\$ or US-5466631-\$ or US-5453394-\$ or US-5439843-\$ or US-5399231-\$ or US-5395481-\$ or US-5391257-\$ or US-5387555-\$ or US-5374581-\$ or US-5374329-\$ or US-5371037-\$ or US-5366924-\$ or US-5324678-\$ or US-5310446-\$ or US-5308776-\$ or US-5277748-\$ or US-5258322-\$ or US-5244817-\$ or US-5250460-\$ or US-5229305-\$ or US-5168078-\$ or US-5098861-\$ or US-4829018-\$ or US-4826787-\$ or US-4752590-\$).did. or (US-20020160603-\$ or US-20020137265-\$ or US-20020096717-\$ or US-20020094663-\$ or US-20020090798-\$ or US-20020086470-\$ or US-20020086469-\$ or US-20020086465-\$ or US-20020072201-\$ or US-20020072200-\$ or US-20020068419-\$ or US-20020048844-\$ or US-20020022344-\$ or US-20020022337-\$ or US-20010021540-\$ or US-20010012677-\$ or US-20010002329-\$).did.) and SOI and (tungsten or W)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 15:28
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